



## Office of Nonproliferation Research and Development

### Overview

### Radiation Detection Materials Development Sandia National Laboratories

**John Goldsmith**

**Manager, Radiation & Nuclear Detection Materials & Analysis Department  
(Livermore, California)**

**(See me regarding detection systems and/or active interrogation)**

Sandia is a multiprogram laboratory operated by Sandia Corporation, a Lockheed Martin Company,  
for the United States Department of Energy's National Nuclear Security Administration  
under contract DE-AC04-94AL85000.





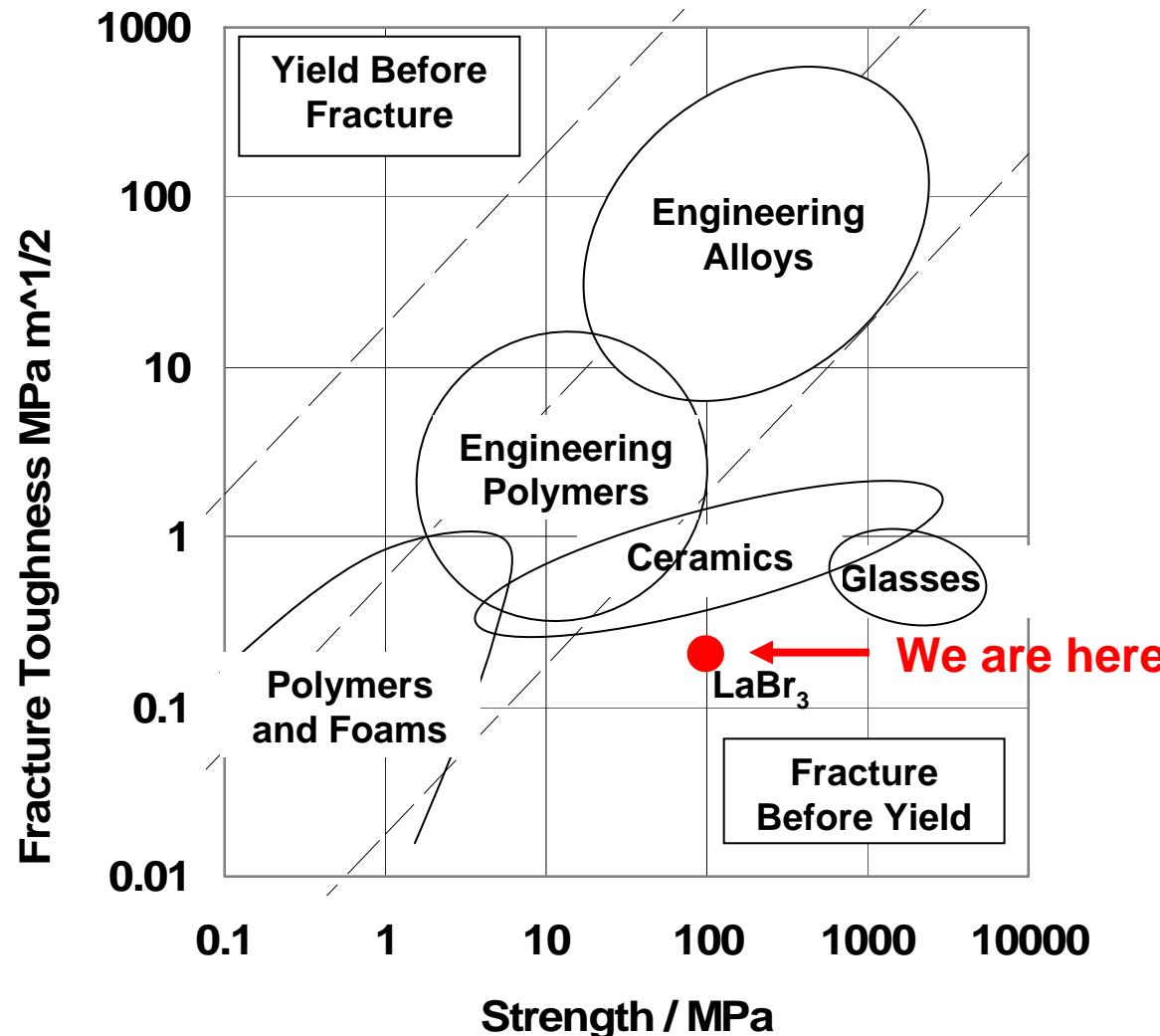
# Lanthanide Halide Scintillators



- **Principal Investigator: Patrick Doty**
- **Collaborators:**
  - Xiaowang Zhou, Pin Yang, Paul Allison (MSU graduate student intern), Sandia
  - Mark Harrison / Doug McGregor, Kansas State University
  - Shawn Kilpatrick / David Bahr, (previously at) Washington State University
  - Raulf Polichar, SAIC
- **Goal: overcome the barriers to production of sensitive gamma ray scintillation spectrometers, through a coordinated program of structure/property analyses, modeling and crystal growth**
- **Funding: Advanced Materials Portfolio, NA-22 (Bob Mayo)**



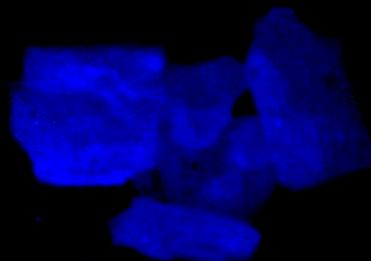
# Lanthanum Bromide



- Failure mechanism initiated by slip on prismatic fracture planes
- 3.7:1 anisotropy in coefficient of thermal expansion
- One solution: aliovalent hardening

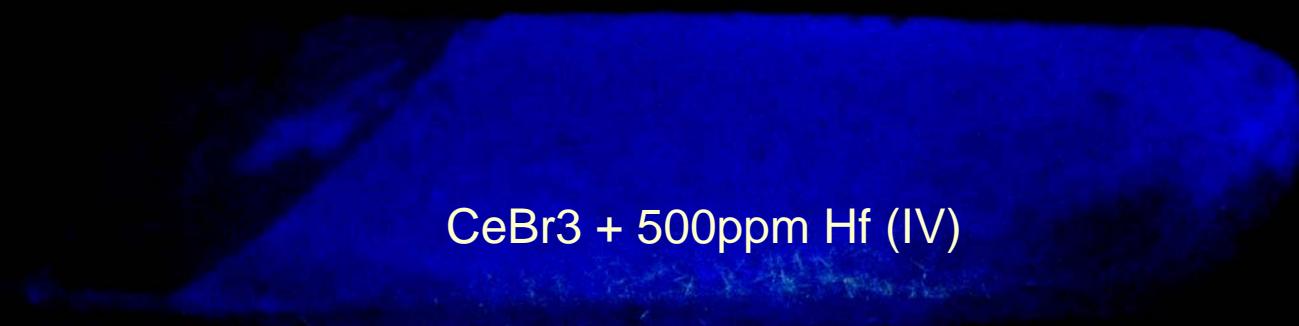


**Strengthening agents increased unfractured size from  $\leq 1$  centimeter to several inches**

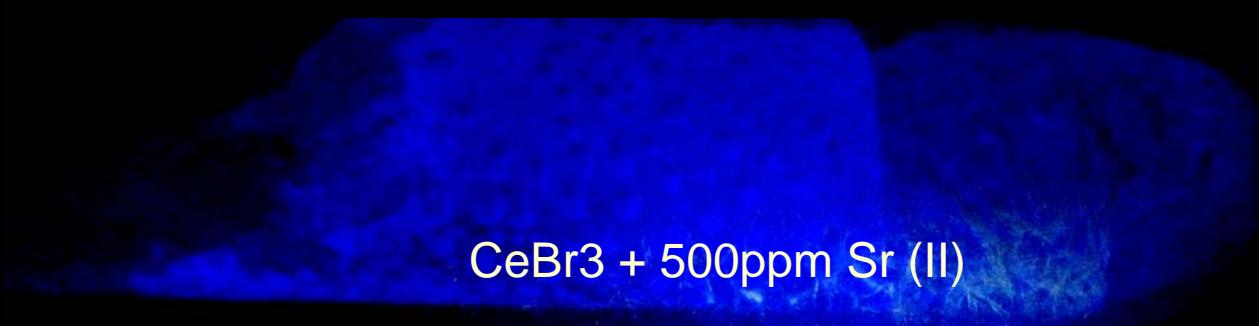


$\text{CeBr}_3$

UV luminescence images



$\text{CeBr}_3 + 500\text{ppm Hf (IV)}$



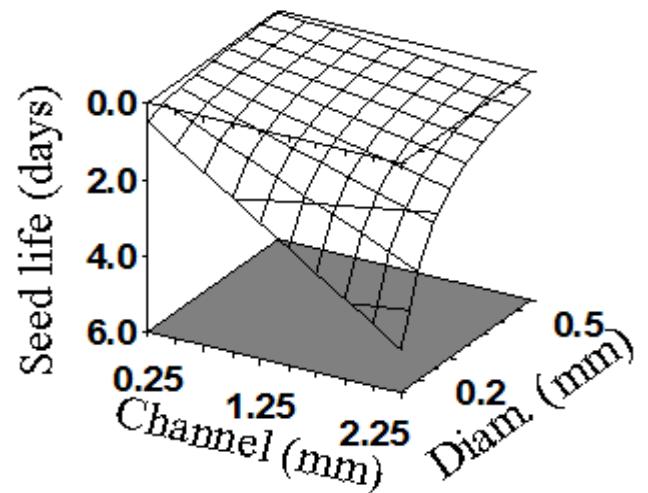
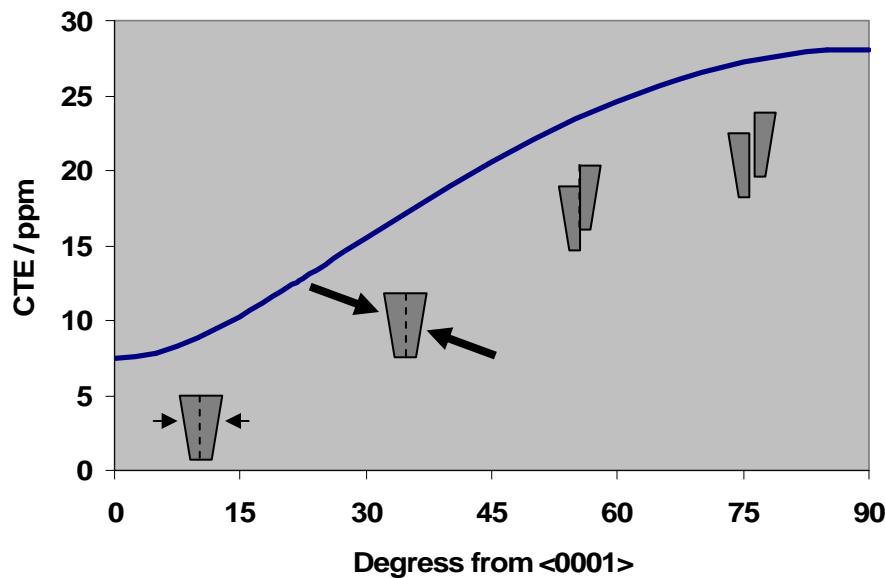
$\text{CeBr}_3 + 500\text{ppm Sr (II)}$

1 inch

# Another approach: seeded growth

**Problem: Large anisotropy of thermal expansion results in shear force on cleavage planes if gradient is not aligned with c-axis**

- Pure compression for c-axis growth
- Both magnitude and orientation of stress increase rapidly for off-axis growth



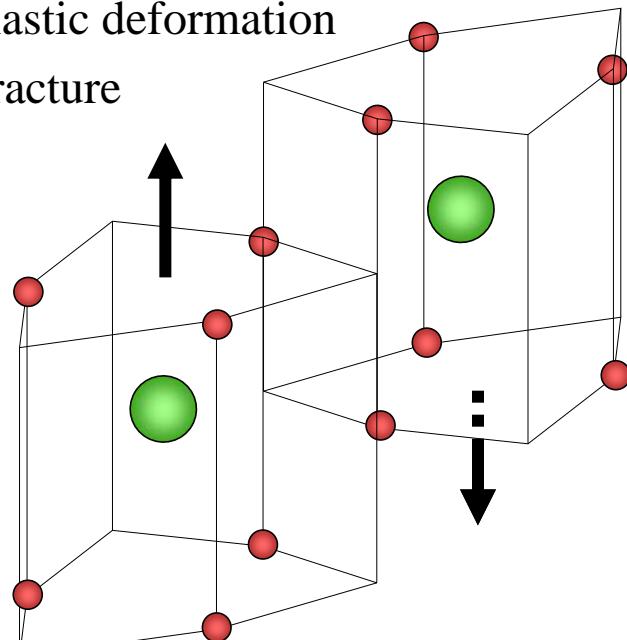


# Model development



**Problem: Develop modeling approach to simulate mechanics of  $LnX_3$  crystals**

- Thermal stress during growth
- Slip systems and dislocation reactions
- Plastic deformation
- Fracture



*Slip and Fracture in  $LnX_3$*

## 1st generation ionic potentials: Fixed Charge

- Overestimates cohesive energy by factor of four!
- Stoichiometric compositions ONLY
- Can not treat defects

## 2nd generation: Variable Charge

- Charges solved by minimizing potential for each  $\delta t$
- *Computationally VERY expensive.*
- Energy is not rigorously conserved!

## 3rd generation: This Work

The embedded ion method that we are developing solves these problems

- Equilibrium charges are analytically integrated:
- No energy minimization is required
- Energy is rigorously conserved

**100 ns time scale, 1,000,000 atoms**



# Materials Science of Elpasolite Scintillators



- **Principal Investigator: Patrick Doty**
- **Collaborators:**
  - Xiaowang Zhou, Pin Yang, Sandia
  - Kanai Shah, RMD
- **Goal develop a fundamental understanding of the composition-structure-property relationships for elpasolite family scintillators**
- **Funding: Advanced Materials Portfolio, NA-22 (Bob Mayo)**
  - New start (FY09)

# Extending embedded-ion method

## Goldschmidt criterion for perovskite

$$0.8 < \frac{R_A + R_X}{\sqrt{2}(R_B + R_X)} < 0.9$$

## Complimentary experimental criteria

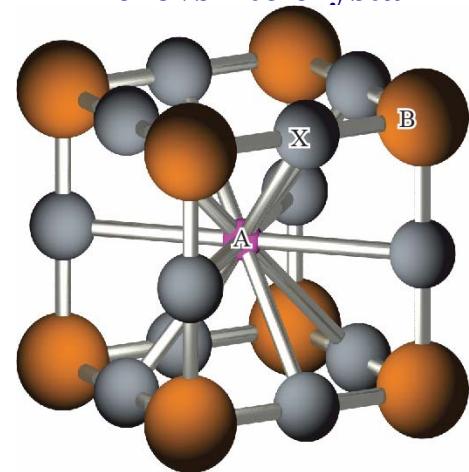
$$0.414 < R_B/R_X < 0.732, \quad R_B/R_X < 1.203 R_A/R_X - 0.488, \quad \text{and}$$

$$4.483(\chi_X - \chi_B)/(\chi_X + \chi_B) + 17.889R_B/(R_X + R_B) - 2.063R_A/(R_X + R_B) > 6.088$$

L. Liang, L. Wencong, and C. Nianyi, *J. Phys. Chem. Solids*, **65**, 855(2004).

Here R is atom radius, and  $\chi$  is electronegativity

## Perovskite crystal



## Embedded-ion method

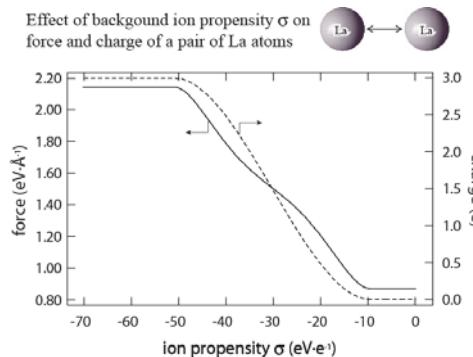
$$E = \frac{1}{2} \sum_{i=1}^N \sum_{\substack{j=1 \\ j \neq i}}^N \phi_{ij}(r_{ij}) + \sum_{i=1}^N E_{emb,i}(\sigma_i), \quad \sigma_i = \sum_{j=1}^N F_j(\chi_j, J_j, r_{ij})$$

$$\phi_{ij}(r) = \frac{E_{b,ij}\beta_{ij}}{\beta_{ij} - \alpha_{ij}} \exp\left[-\alpha_{ij}\left(r - \frac{R_i + R_j}{2}\right)\right] - \frac{E_{b,ij}\alpha_{ij}}{\beta_{ij} - \alpha_{ij}} \exp\left[-\beta_{ij}\left(r - \frac{R_i + R_j}{2}\right)\right]$$

$\phi$ : pair energy function;  $E_{emb}$ : embedding energy function;  $\sigma_i$ : ion propensity at site i;  $F$ : a function characterizing the ionic properties of the atom;  $\chi$ ,  $J$ ,  $E_b$ ,  $\alpha$ ,  $\beta$ ,  $R$ : parameters.

Note R and  $\chi$  are input parameters and crystal prediction will be output.

## Reactivity incorporated



Correctly predict the ionization of the La atoms and the associated repulsive force at a strong negative ion propensity environment.



# Fission Neutron Detection using Heteroepitaxial Chemical Vapor Deposition Diamond



- **Principal Investigator:** Richard Anderson
- **Collaborators:**
  - Brage Golding, Michigan State University
- **Goal:** synthesize large-area, defect-free single crystal diamond on low-cost non-diamond substrates (heteroepitaxy)
- **Funding:** DNDT Transformational and Applied Research Directorate

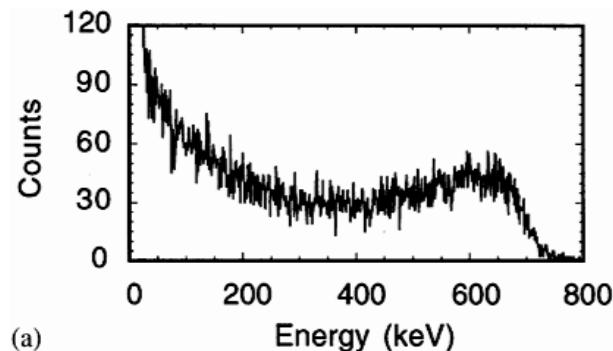
**Note: Brage speaking tomorrow at 8:40 am**



# Single crystal diamond is the best spectroscopic SNM neutron detector



Efficiency	<ul style="list-style-type: none"><li>Efficient energy transfer to the recoiling diamond nucleus (up to 28%)</li><li>Highest scattering efficiency of any material: 6.1% of 0.1 - 1 MeV neutrons lose energy per mm diamond</li></ul>
<u>Semi-conductor Detection</u>  <u>Charge Collection is Key</u>	<ul style="list-style-type: none"><li>High mobility*<ul style="list-style-type: none"><li>4500 cm<sup>2</sup>/V-sec electrons</li><li>3800 cm<sup>2</sup>/V-sec holes</li></ul></li><li>Long lifetime* - <math>\mu</math>sec</li></ul>
Linearity	• 4.8 MeV threshold for inelastic scattering
Gamma Insensitive	Yes, Z = 6



Single Pixel Counts vs. energy deposited, 2.5 MeV neutrons in CVD diamond crystal. G. J. Schmid et al., *Nucl. Instr. And Meth. A527* (2004), pp 554-561.

Problem: Growing diamond on diamond (homoepitaxy) not practical for large-size detectors

**Solution: Scaling by synthesis on non-diamond substrates (heteroepitaxy)**

\*Isberg et al. *Science* 297 (2002) 1670. : CVD homoepitaxial diamond--room temperature



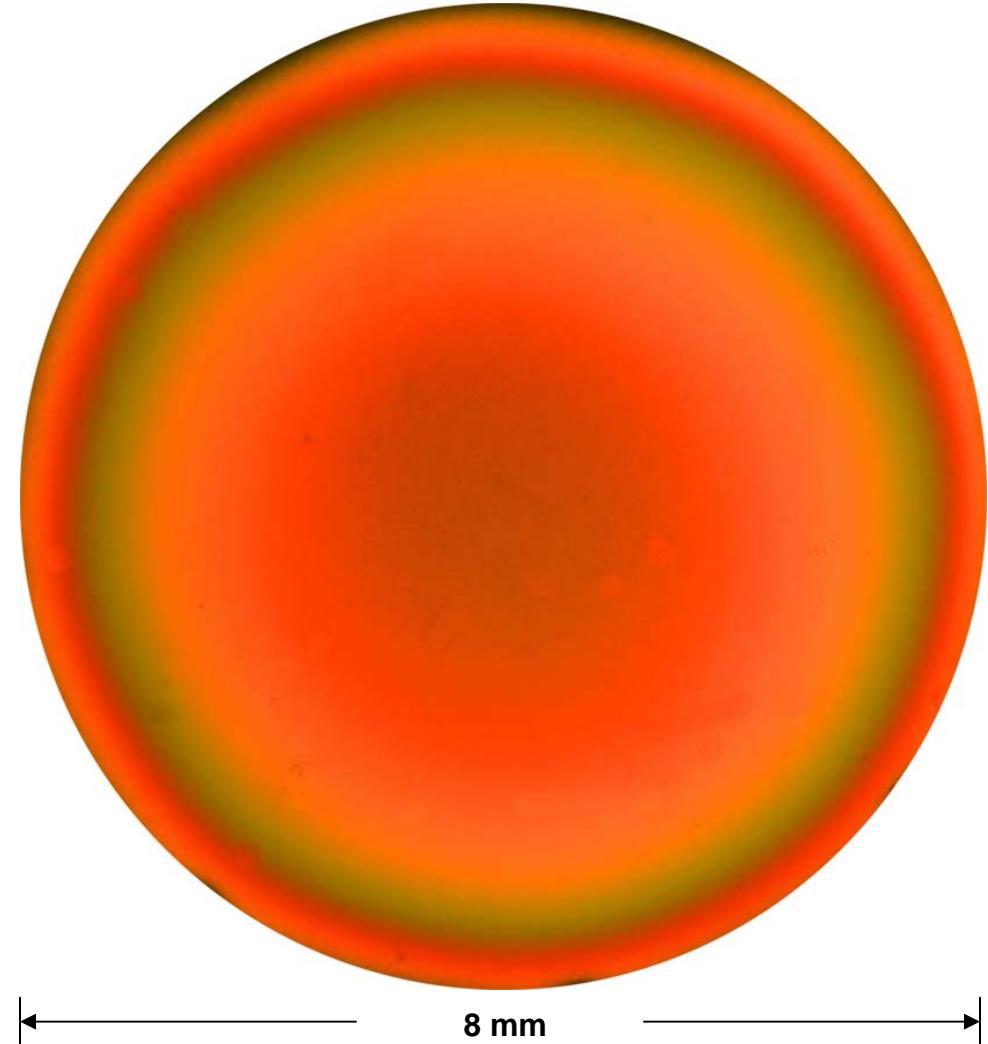
# Large, high uniformity diamond grown by heteroepitaxy



**600 nm thick single crystal  
grown by heteroepitaxial CVD**

**Highly uniform across 8 mm  
diameter**

**Will act as “seed” for  
homoepitaxial growth**





# Structural Origins of Scintillation: Metal Organic Frameworks as a Nanolaboratory



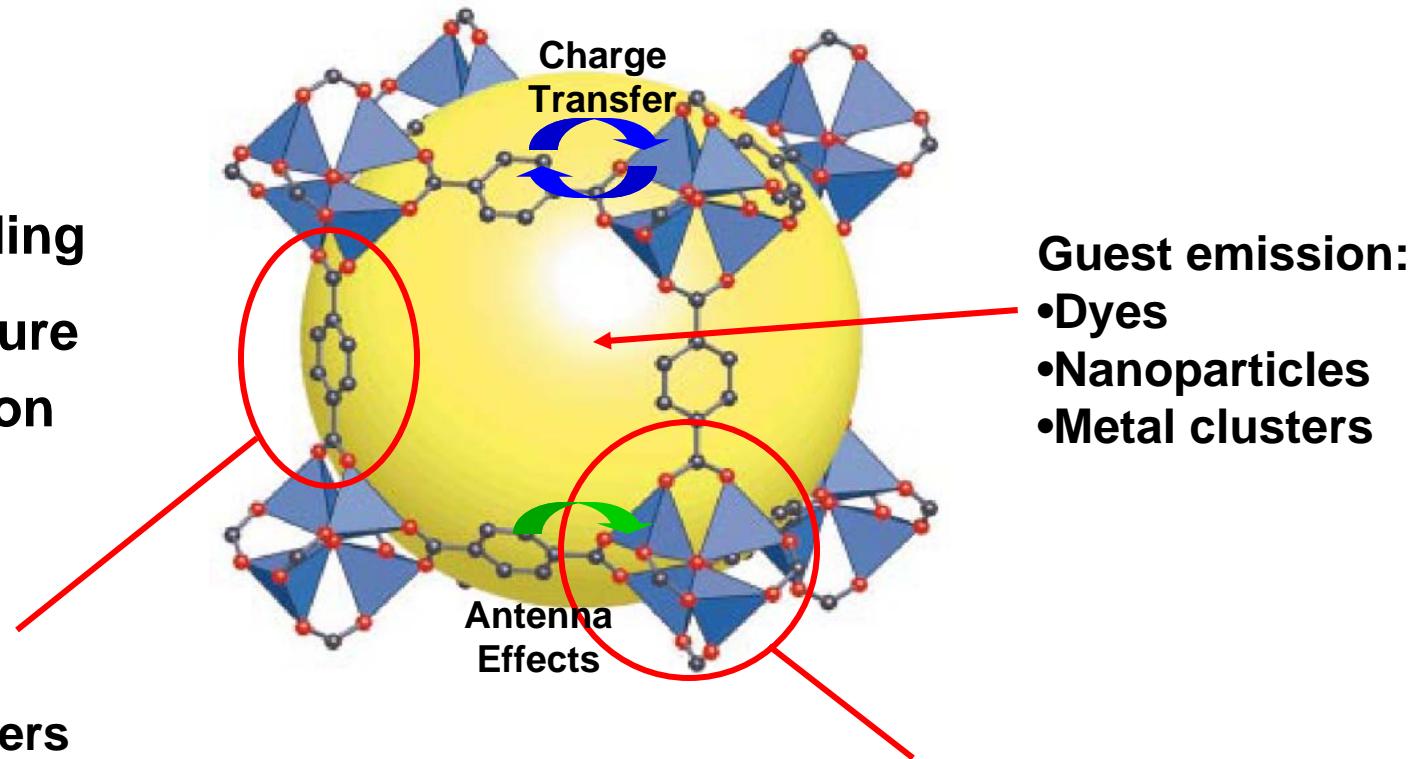
- **Principal Investigator: Patrick Doty**
- **Collaborators:**
  - Mark Allendorf, Ron Houk, Rago Bhakta, Ida Nielsen, George Vizkelethy, and Barney Doyle, Sandia
- **Goal: develop tools and techniques that elucidate fundamental processes in organic scintillators through studies of metal organic framework materials (MOFs), and enable the characterization and control of the growth and synthesis processes for fast neutron scintillators and other potential sensor materials**
- **Funding: DTRA Basic and Applied Sciences Directorate**



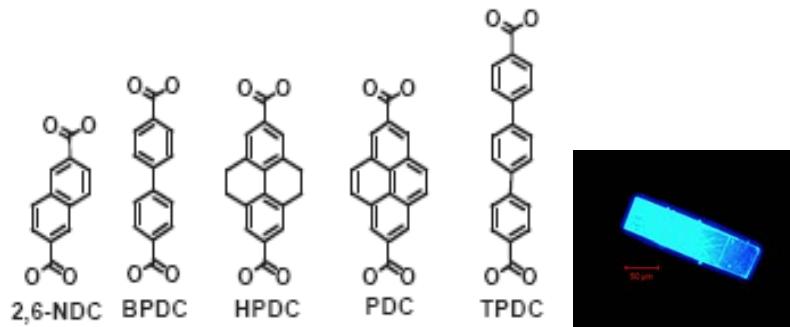
# Why are MOFs interesting for sensing applications?



- Strong bonding
- Tailor structure for application



## Fluorescent Linkers



- Coordinating Metal:**
- Transition metals
  - Lanthanides
  - Open coordination sites

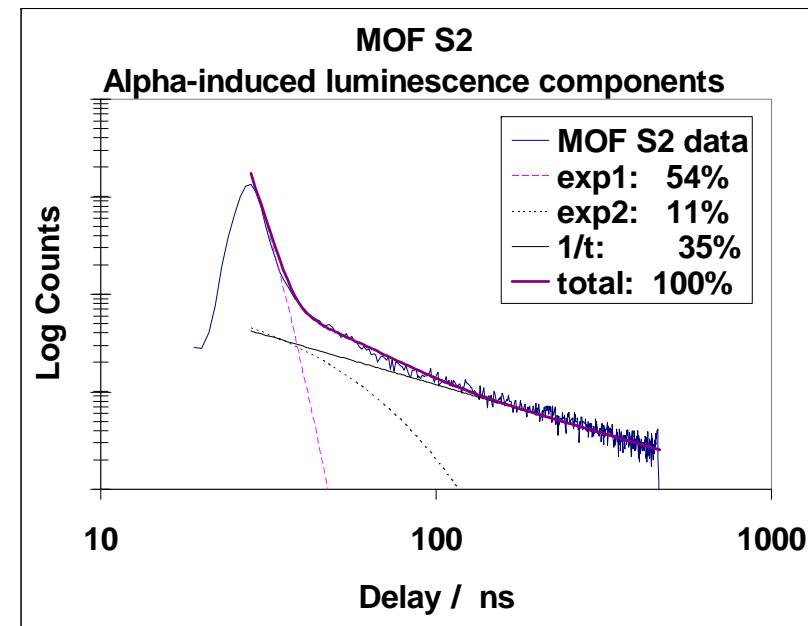
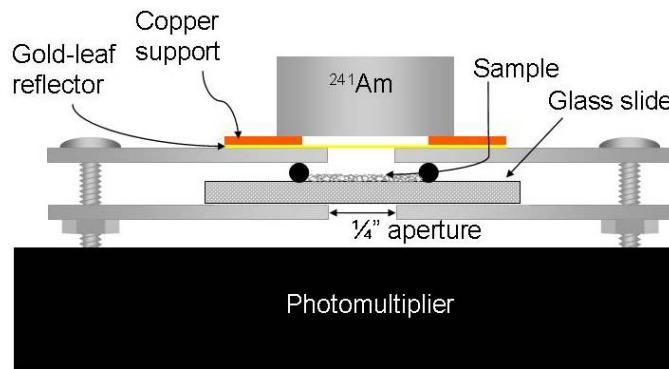


# Local MOF environment controls scintillation timing



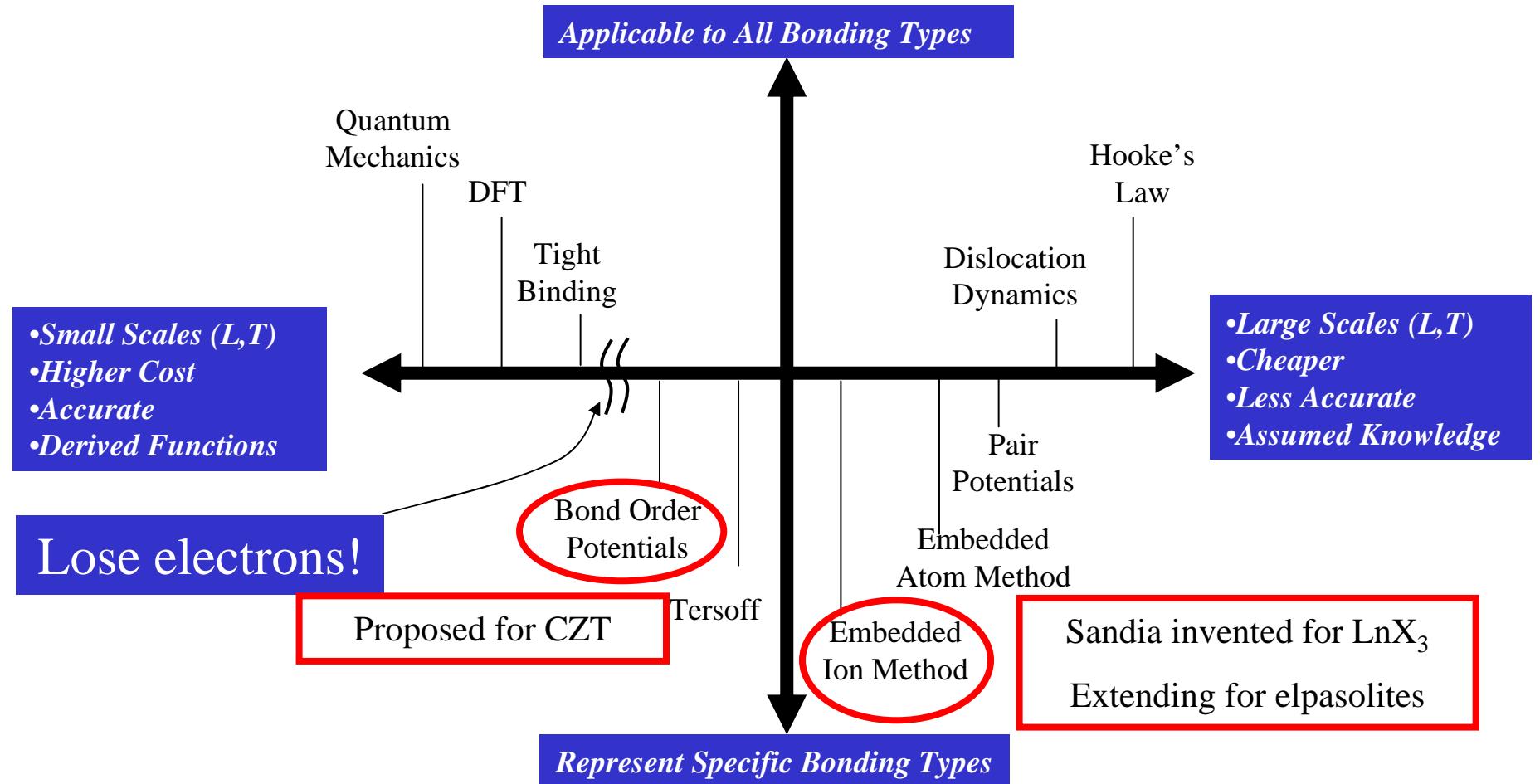
- Timing data obtained by exposure to  $\alpha$  particles
- **MOF-S1:** Exponential decay of fast component
- **MOF-S2:** Scintillation pulses observed on two different time scales:
  - Fast ( $< 1 \mu\text{s}$ ): biexponential decay
  - Slow ( $>> 1 \mu\text{s}$ ):  $1/t$
- Slow component may be the result of electron tunneling

→ Pulse-shape discrimination may be controllable via MOF crystal structure





# Modeling approaches (halides)

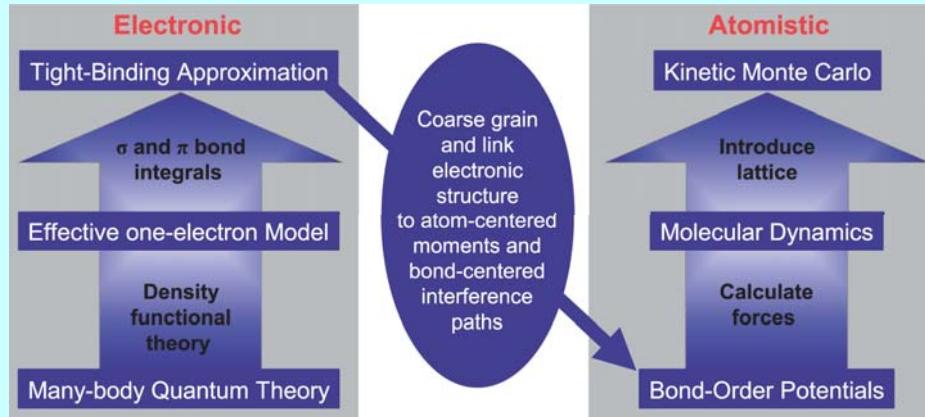




# Bond order potential for covalent systems



## BOP Is a Quantum-mechanically Derived Potential



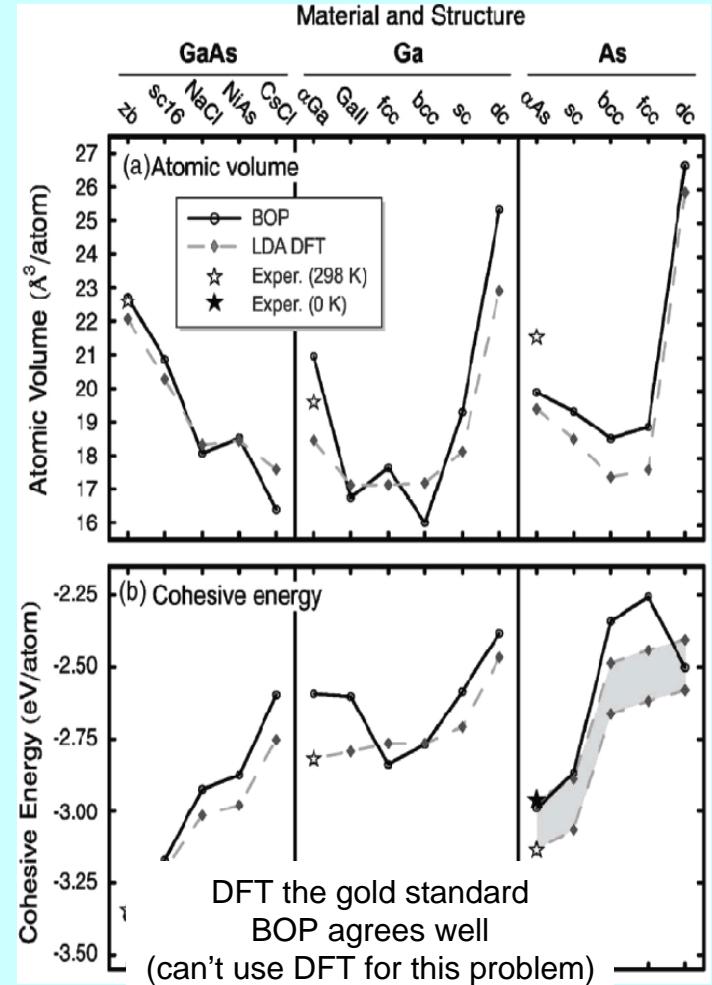
Can incorporate:  $\sigma$  bonding,  $\pi$  bonding, promotion energy, environment dependence, dihedral angle, and more...

Defect types	DFT	BOP
$V_{\text{Ga}}$	3.15	3.28
$V_{\text{As}}$	3.10	2.93
$\text{Ga}_{\text{As}}$	2.12	2.03
$\text{As}_{\text{Ga}}$	2.48	2.50
$\text{Ga}_i$ (tetrahedral)	2.98	2.66
		4.14
$\text{As}_i$ (tetrahedral)	5.04	4.47
		3.32
$\text{Ga}_i$ ((110) dumbbell)	3.53	4.97
$\text{As}_i$ ((110) dumbbell)	4.07	3.82
$\text{Ga}_i$ ((100) dumbbell)	-	3.86
$\text{As}_i$ ((100) dumbbell)	-	4.68

## The Only Predictive Potential for Defects

- D. G. Pettifor, Phys. Rev. Lett., 63, 2480 (1989).
- D. G. Pettifor, and I. I. Oleinik, Phys. Rev. B, 59, 8487 (1999).
- D. G. Pettifor, and I. I. Oleinik, Phys. Rev. B, 65, 172103 (2002).
- I. I. Oleinik, and D. G. Pettifor, Phys. Rev. B, 59, 8500 (1999).
- D. G. Pettifor, and I. I. Oleinik, Phys. Rev. Lett., 84, 4124 (2000).
- D. A. Murdick, X. W. Zhou, H. N. G. Wadley, D. Nguyen-Manh, R. Drautz, and D. G. Pettifor, Phys. Rev. B, 73, 45206(2006).
- D. A. Murdick, H. N. G. Wadley, and X. W. Zhou, Phys. Rev. B, 75, 125318(2007).

## The Only Transferrable Potential





## Not currently active:



- Organic scintillators for neutron spectroscopy (former DND0 project)
- Ceramic lanthanum halide scintillators (former DND0 project)
- Organic semiconductors for neutron counting (LDRD)
- Modeling of trapping mechanisms in CZT (proposed)



# Materials capabilities at Sandia



- Computational Materials Science
- X-ray powder diffraction and structure analysis of hygroscopic materials
- X-ray single crystal rocking curves
- Electron microscopy and microanalysis
- Thermal analysis techniques
- Thermomechanical property evaluation
- Microhardness and fracture strength
- Spectroscopic evaluations including fluorimetry and time correlated radioluminescence characterization
- Electronic measurements of solid-state detector materials including current-voltage, capacitance-voltage, photoconductivity, mobility and trapping time
- Low temperature studies including photoluminescence and thermally-stimulated current
- Organic and inorganic synthesis

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User facility: <http://www.sandia.gov/bus-ops/partnerships/tech-access/facilities/radiation.html>